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# BC337 / BC338 NPN Epitaxial Silicon Transistor

## Features

- Switching and Amplifier Applications
- Suitable for AF-Driver Stages and Low-Power Output Stages
- Complement to BC327 / BC328



## Ordering Information

Part Number	Top Mark	Package	Packing Method
BC33716BU	BC33716	TO-92 3L	Bulk
BC33716TA	BC33716	TO-92 3L	Ammo
BC33716TFR	BC33716	TO-92 3L	Tape and Reel
BC33725BU	BC33725	TO-92 3L	Bulk
BC33725TA	BC33725	TO-92 3L	Ammo
BC33725TAR	BC33725	TO-92 3L	Ammo
BC33725TF	BC33725	TO-92 3L	Tape and Reel
BC33725TFR	BC33725	TO-92 3L	Tape and Reel
BC33740BU	BC33740	TO-92 3L	Bulk
BC33740TA	BC33740	TO-92 3L	Ammo
BC33825TA	BC33825	TO-92 3L	Ammo

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-Emitter Voltage	BC337	50
		BC338	30
$V_{CEO}$	Collector-Emitter Voltage	BC337	45
		BC338	25
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_C$	Collector Current (DC)	800	mA
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55 to 150	$^\circ\text{C}$

BC337 / BC338 — NPN Epitaxial Silicon Transistor

**Thermal Characteristics<sup>(1)</sup>**

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$P_D$	Power Dissipation	625	mW
	Derate Above $25^\circ\text{C}$	5.0	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	$^\circ\text{C}/\text{W}$

**Note:**

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

**Electrical Characteristics**

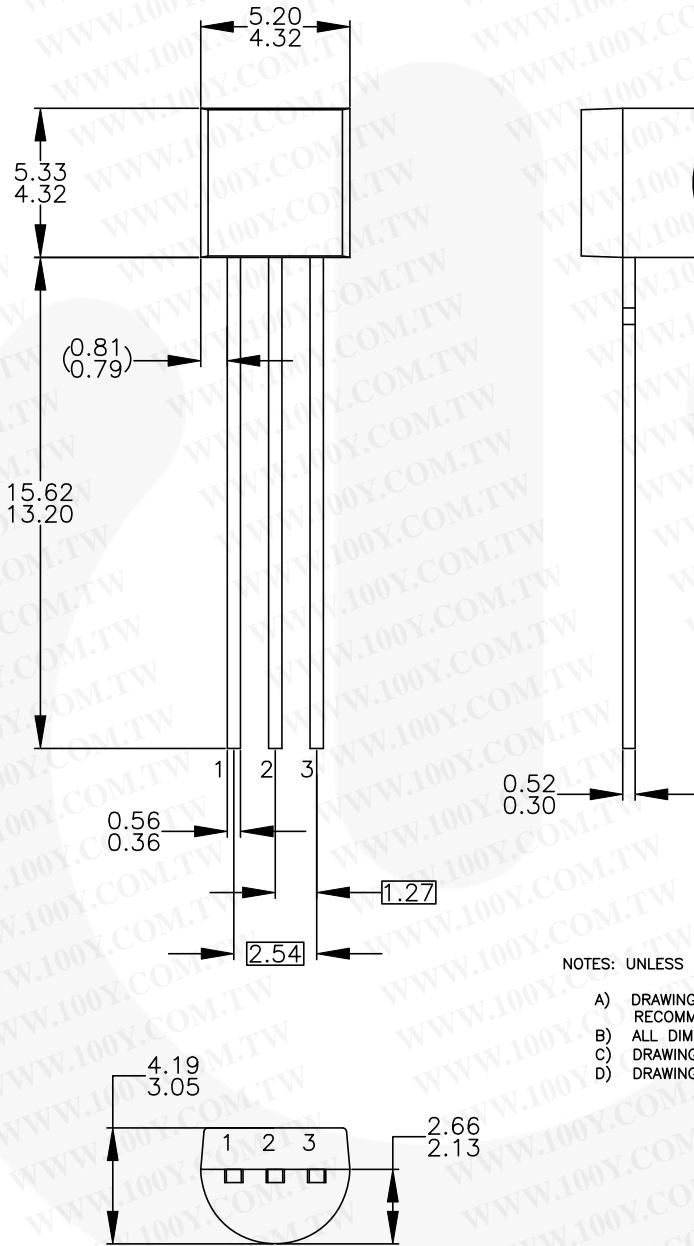
Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit	
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	BC337	$I_C = 10\text{ mA}, I_B = 0$	45			V
		BC338		25			
$BV_{CES}$	Collector-Emitter Breakdown Voltage	BC337	$I_C = 0.1\text{ mA}, V_{BE} = 0$	50			V
		BC338		30			
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 0.1\text{ mA}, I_C = 0$	5			V	
$I_{CES}$	Collector Cut-Off Current	BC337	$V_{CE} = 45\text{ V}, I_B = 0$		2	100	nA
		BC338	$V_{CE} = 25\text{ V}, I_B = 0$		2	100	
$h_{FE1}$	DC Current Gain		$V_{CE} = 1\text{ V}, I_C = 100\text{ mA}$	100		630	
$h_{FE2}$			$V_{CE} = 1\text{ V}, I_C = 300\text{ mA}$	60			
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$			0.7	V	
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 1\text{ V}, I_C = 300\text{ mA}$			1.2	V	
$f_T$	Current Gain Bandwidth Product	$V_{CE} = 5\text{ V}, I_C = 10\text{ mA}, f = 50\text{ MHz}$		100		MHz	
$C_{ob}$	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		12		pF	

 **$h_{FE}$  Classification**

Classification	16	25	40
$h_{FE1}$	100 ~ 250	160 ~ 400	250 ~ 630
$h_{FE2}$	60 ~	100 ~	170 ~

Physical Dimensions



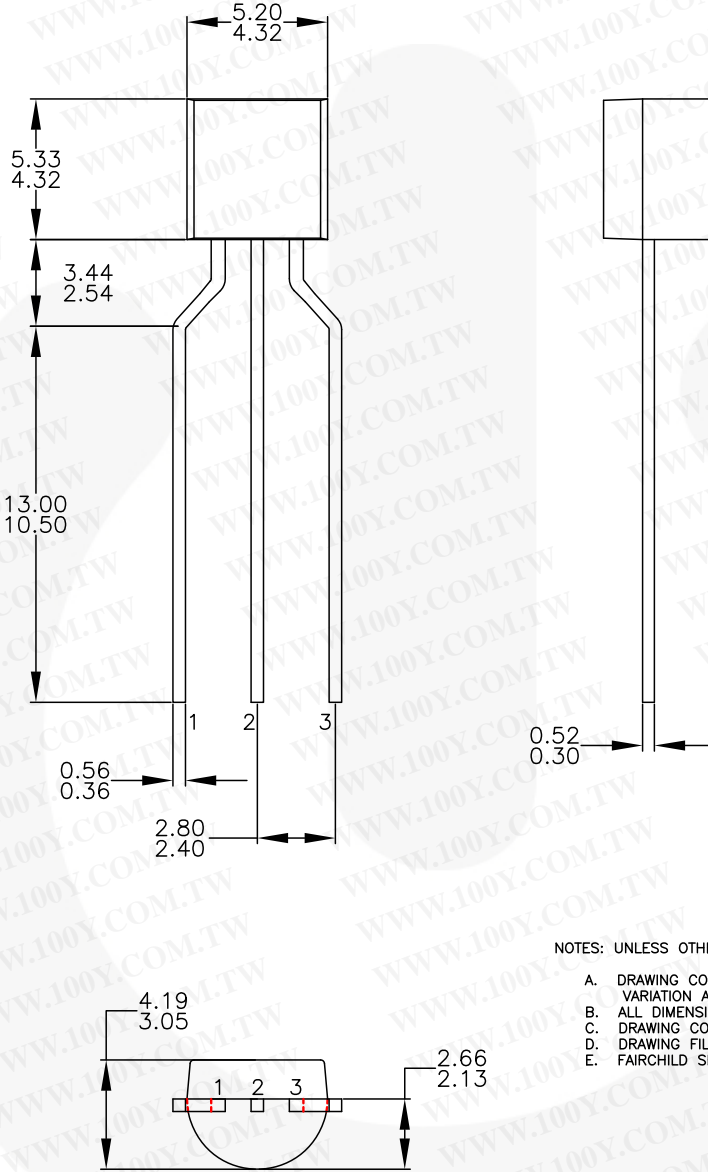
NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-2009.
- D) DRAWING FILENAME: MKT-ZA03DREV4.



Figure 1. 3-Lead, TO-92, JEDEC TO-92 Compliant Straight Lead Configuration, Bulk Type

Physical Dimensions (Continued)



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. FAIRCHILD SEMICONDUCTOR.

Figure 2. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Type

